

Fig. 1.

Growth of multiple non-compositional-graded layers

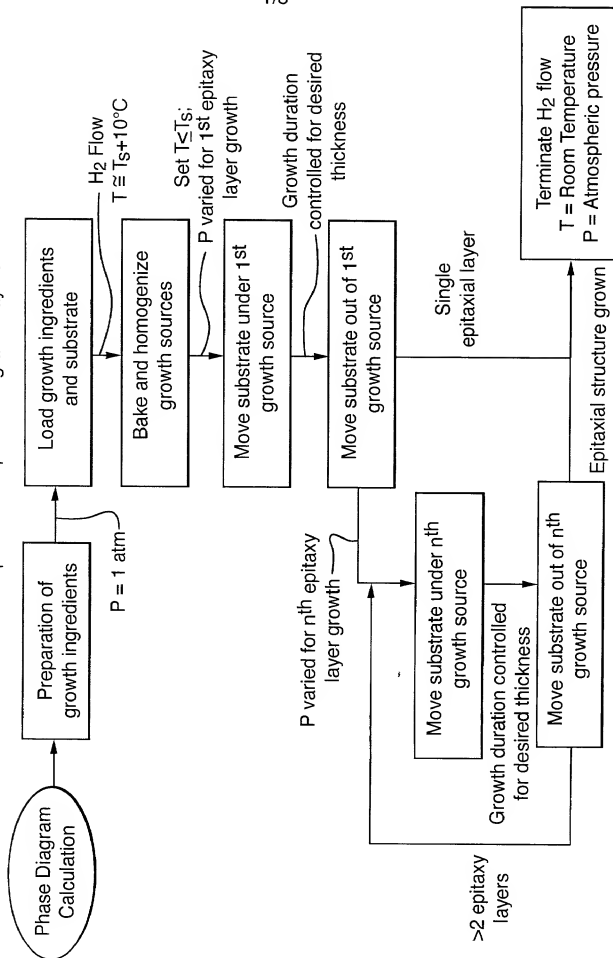


Fig.2.

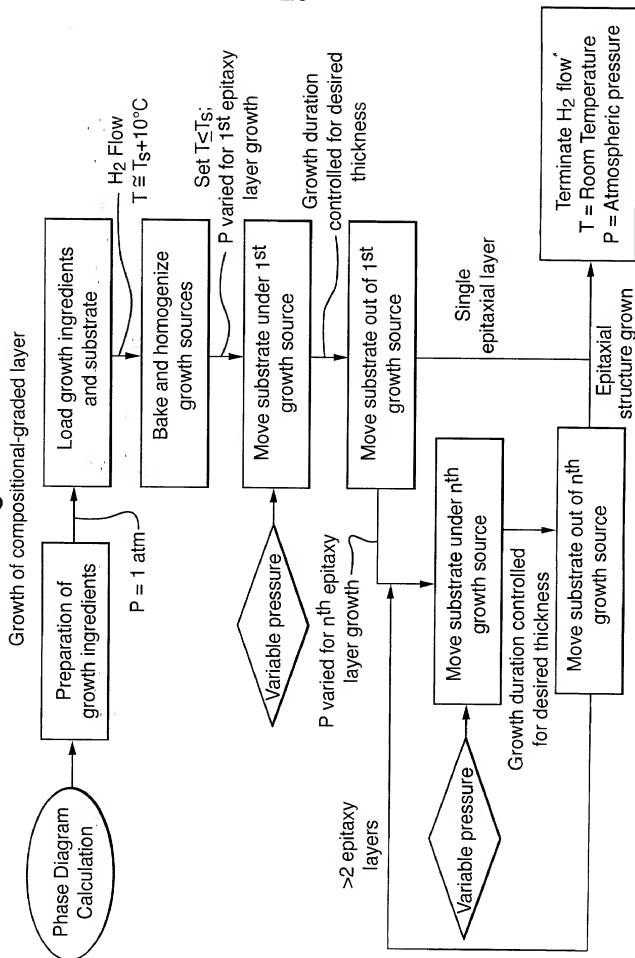


Fig.3.

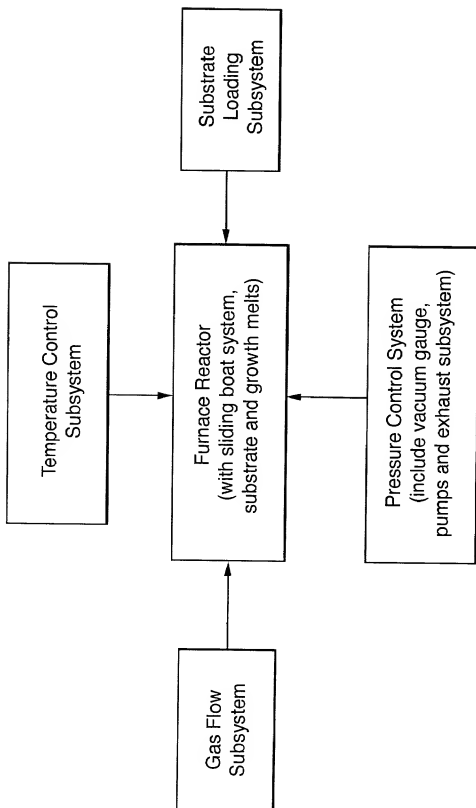
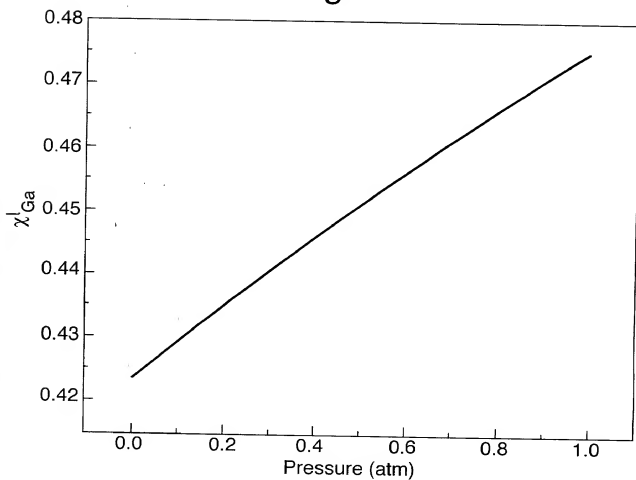
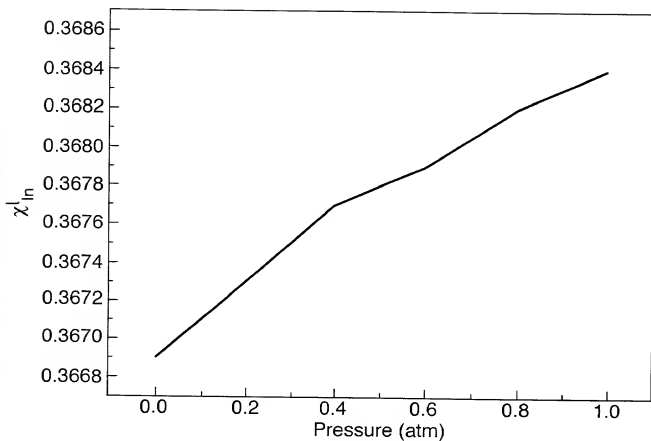


Fig.4.



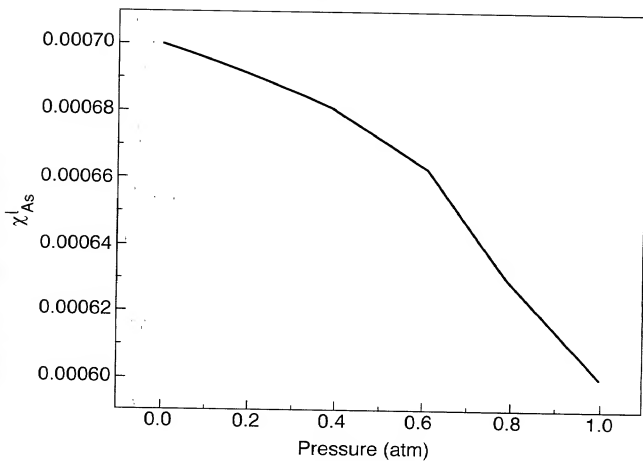
Atomic fraction χ_{Ga}^l in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.5.



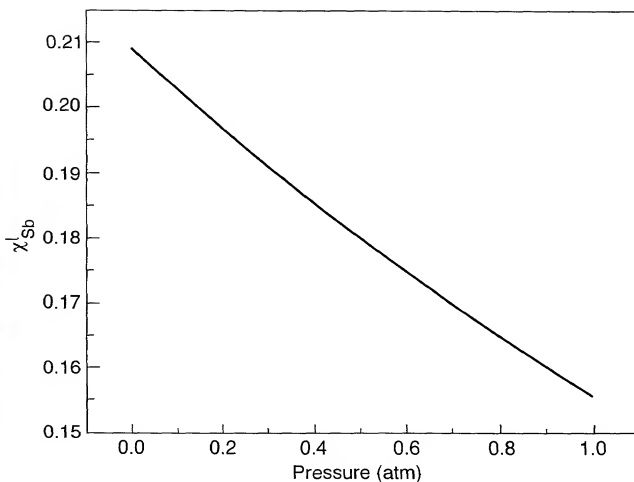
Atomic fraction χ_{In} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.6.



Atomic fraction χ_{As}^l in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.7.



Atomic fraction χ_{Sb}^l in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.8(a).

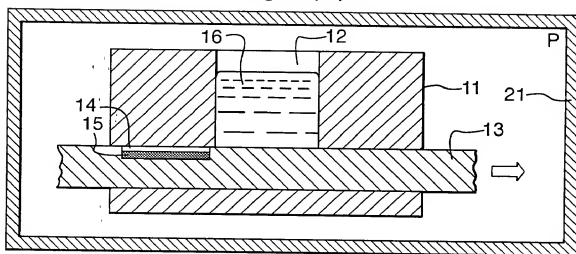


Fig.8(b).

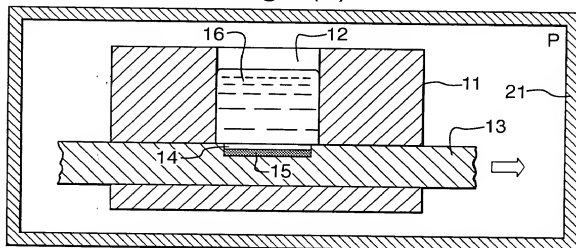


Fig.8(c).

